Norbert Esser

List of Publications by Year
in descending order

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241	5,068	76326	161849
papers	citations	40	54
		h-index	g-index

251	251	251	3818
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Band-gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mrow><mml:mn>10</mml:mn></mml:mrow><mml:mn>20</mml:mn></mml:msup><mml:mathvariant="normal">cm</mml:mi><mml:msup><mml:mrow /><mml:mrow><mml:mo>â^’</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:msup></mml:math>. Physical Review B, 2014, 90, .	3.2	133
2	Optical properties of copper and silver in the energy range 2.5â€“9.0 eV. Physical Review B, 2001, 64, .	3.2	116
3	Reflectance Anisotropy of GaAs(100): Theory and Experiment. Physical Review Letters, 1998, 81, 721-724.	7.8	106
4	Understanding reflectance anisotropy: Surface-state signatures and bulk-related features in the optical spectrum ofInP(001)(2Ã—4). Physical Review B, 2000, 61, R16335-R16338.	3.2	87
5	Dielectric function of wurtzite GaN and AlN thin films. Solid State Communications, 1999, 112, 129-133.	1.9	82
6	Structural properties of chalcopyrite thin films studied by Raman spectroscopy. Physica Status Solidi (B): Basic Research, 2005, 242, 2633-2643.	1.5	82
7	Analysis of Organic Films and Interfacial Layers by Infrared Spectroscopic Ellipsometry. Applied Spectroscopy, 2005, 59, 272A-282A.	2.2	80
8	InP(001)-(2Ã—1) Surface: A Hydrogen Stabilized Structure. Physical Review Letters, 2003, 90, 126101.	7.8	68
9	Surface optical properties of clean Cu(110) and Cu(110)-(2Ã—1)-O. Physical Review B, 2000, 61, 3043-3047.	3.2	67
10	Ellipsometric studies ofBexZn1â^’xSebetween 3 eV and 25 eV. Physical Review B, 1999, 59, 10071-10075.	3.2	66
11	Atomic structure of InP(001)-(2Ã—4): A dimer reconstruction. Physical Review B, 1998, 57, 14596-14599.	3.2	64
12	Anisotropic absorption and emission of bulk<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo>(</mml:mo><mml:mn>1</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 297 Td Physical Review B, 2013, 87, .	3.2	61
13	Anisotropy of the dielectric function for wurtzite InN. Superlattices and Microstructures, 2004, 36, 591-597.	3.1	60
14	Spectroscopic ellipsometry measurements of Al Ga1â^’N in the energy range 3â€“25 eV. Thin Solid Films, 1998, 313-314, 745-750.	1.8	59
15	(2Ã—4)GaP(001) surface: Atomic structure and optical anisotropy. Physical Review B, 1999, 60, 2488-2494.	3.2	58
16	Raman monitoring of semiconductor growth. Journal of Applied Physics, 1994, 75, 7330-7333.	2.5	57
17	Dielectric function and Van Hove singularities for In-richInxGa1â^’xNalloys: Comparison of N- and metal-face materials. Physical Review B, 2007, 75, .	3.2	56
18	Optical properties of cubic GaN from 1 to 20 eV. Physical Review B, 2012, 85, .	3.2	55

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19	In Situ Infrared Ellipsometric Study of Stimuli-Responsive Mixed Polyelectrolyte Brushes. Analytical Chemistry, 2007, 79, 7676-7682.	6.5	54
20	Dielectric function of zinc-blende AlN from 1 to 20 eV: Band gap and van Hove singularities. Journal of Applied Physics, 2009, 106, 076104.	2.5	54
21	GaAs(001): Surface Structure and Optical Properties. Physica Status Solidi A, 2001, 188, 1401-1409.	1.7	53
22	Detailed analysis of the dielectric function for wurtzite InN and In-rich InAlN alloys. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 42-49.	1.8	53
23	Atomic surface structure of the phosphorous-terminated InP(001) grown by MOVPE. Physical Review B, 1999, 60, R5117-R5120.	3.2	52
24	GaN<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>m</mml:mi></mml:math>-plane: Atomic structure, surface bands, and optical response. Physical Review B, 2015, 91, .	3.2	52
25	GaP(001) and InP(001): Reflectance anisotropy and surface geometry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1691.	1.6	50
26	Optical properties of MgZnO alloys: Excitons and exciton-phonon complexes. Journal of Applied Physics, 2011, 110, .	2.5	50
27	Surface quality and atomic structure of MBE-grown GaAs(100) prepared by the desorption of a protective arsenic layer. Surface Science, 1996, 352-354, 71-76.	1.9	49
28	Atomic Structure of the Sb-Stabilized GaAs(100)-(2Ã—4) Surface. Physical Review Letters, 1996, 77, 4402-4405.	7.8	48
29	Dielectric function of hexagonal AlN films determined by spectroscopic ellipsometry in the vacuum-uv spectral range. Physical Review B, 1999, 59, 1845-1849.	3.2	48
30	Phonon and polarized reflectance spectra fromSi(111)â^'(4Ã—1)In:â€,â€,Evidence for a charge-density-wave driven phase transition. Physical Review B, 2003, 67, .	3.2	48
31	Identification of van Hove singularities in the GaN dielectric function: a comparison of the cubic and hexagonal phase. Physica Status Solidi (B): Basic Research, 2009, 246, 1440-1449.	1.5	48
32	Optical spectra of ZnO in the far ultraviolet: First-principles calculations and ellipsometric measurements. Physical Review B, 2010, 81, .	3.2	48
33	Arsenic passivation of MBE grown GaAs(100): structural and electronic properties of the decapped surfaces. Surface Science, 1992, 269-270, 797-803.	1.9	47
34	Near valence-band electronic properties of semiconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:msub><mml:mrow><mml:mo>â^'</mml:mo></mml:mrow><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(100) single crystals. Physical Review B, 2015, 92, .	3.2	47
35	Surface-state contribution to the optical anisotropy of Ag(110) surfaces: A reflectance-anisotropy-spectroscopy and photoemission study. Physical Review B, 1998, 58, R10207-R10209.	3.2	46
36	Structure of Si(111)-In Nanowires Determined from the Midinfrared Optical Response. Physical Review Letters, 2009, 102, 226805.	7.8	46

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37	Influence of exciton-phonon coupling and strain on the anisotropic optical response of wurtzite AlN around the band edge. Physical Review B, 2011, 83, .	3.2	46
38	Surface properties of annealed semiconducting Î²-Ga2O3 (1 0 0) single crystals for epitaxy. Applied Surface Science, 2015, 349, 368-373.	6.1	46
39	Micro-Raman Study of Orientation Effects of CuxSe-Crystallites on Cu-rich CuGaSe2 Thin Films. Journal of Applied Physics, 2004, 96, 1963-1966.	2.5	42
40	Ellipsometry from infrared to vacuum ultraviolet: Structural properties of thin anisotropic guanine films on silicon. Physica Status Solidi (B): Basic Research, 2005, 242, 2681-2687.	1.5	41
41	Surface Phonons of InP(110) Studied by Raman Spectroscopy. Physical Review Letters, 1997, 79, 1094-1097.	7.8	39
42	Transition energies and direct-indirect band gap crossing in zinc-blende Al<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>N. Physical Review B, 2013, 87, .	3.2	39
43	Reflectance anisotropy spectroscopy of ordered Sb overlayers on GaAs(110) and InP(110). Surface Science, 1994, 307-309, 1045-1050.	1.9	38
44	Dielectric function and critical points of the band structure for AlGaN alloys. Physica Status Solidi (B): Basic Research, 2005, 242, 2610-2616.	1.5	38
45	Critical points of the band structure and valence band ordering at the point of wurtzite InN. Journal of Crystal Growth, 2006, 288, 273-277.	1.5	38
46	Structural and Optical Properties of DNA Layers Covalently Attached to Diamond Surfaces. Langmuir, 2008, 24, 7269-7277.	3.5	38
47	Scanning-tunneling-microscopy study of InP(001) surfaces prepared by UHV decapping of metal-organic vapor-phase-epitaxy-grown samples. Physical Review B, 1996, 53, R13257-R13259.	3.2	37
48	Optical Properties of Ordered As Layers on InP(110) Surfaces. Physical Review Letters, 1996, 77, 759-762.	7.8	37
49	AlGaN-Based Bragg Reflectors. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	37
50	Molecular Orientation in Octanedithiol and Hexadecanethiol Monolayers on GaAs and Au Measured by Infrared Spectroscopic Ellipsometry. Langmuir, 2009, 25, 919-923.	3.5	37
51	Polarization- and Wavelength-Dependent Surface-Enhanced Raman Spectroscopy Using Optically Anisotropic Rippled Substrates for Sensing. ACS Sensors, 2016, 1, 318-323.	7.8	36
52	Optical properties of the Au(110) surface. Physical Review B, 2001, 65, .	3.2	35
53	Optical anisotropy and magneto-optical properties of Ni on preoxidizedCu(110). Physical Review B, 2006, 73, .	3.2	34
54	Controlled growth of ordered monolayers of N-heterocyclic carbenes on silicon. Nature Chemistry, 2021, 13, 828-835.	13.6	34

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55	Dielectric functions of DNA base films from near-infrared to ultra-violet. Physica Status Solidi (B): Basic Research, 2005, 242, 3047-3052.	1.5	33
56	Atomic structure and optical anisotropy of IIIâ€“V(001) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1756.	1.6	31
57	Optical properties of SiC investigated by spectroscopic ellipsometry from 3.5 to 10 eV. Thin Solid Films, 2000, 364, 111-113.	1.8	30
58	Clarification of theGaP(001)(2Ã—4)Ga-rich reconstruction by scanning tunneling microscopy andab initiotheory. Physical Review B, 2000, 62, 11046-11049.	3.2	30
59	Microscopic structure of the GaAs(001)-(6Ã—6) surface derived from scanning tunneling microscopy. Physical Review B, 1995, 51, 13880-13882.	3.2	29
60	Thermal stability and Schottky barrier of Sb overlayers on GaAs(110) and InP(110). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 680.	1.6	28
61	Electronic surface state resonant Raman scattering from vibrational modes of adsorbed monolayers: Sb on IIIâ€“V semiconductors. Solid State Communications, 1992, 84, 165-169.	1.9	28
62	Hydrogen-induced modification of the optical properties of the GaAs(100) surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1666.	1.6	28
63	Surface phonons of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">Si</mml:mi><mml:mrow><mml:mo>(</mml:mo><mml:mn>111</mml:mn><mml:mo>)</mml:mo></mml:mrow><mml:mo>-</mml:mo><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mtext>â^’</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mn>4</mml:mn><mml:mo>×</mml:mo><mml:mn>1</mml:mn><mml:mo>)</mml:mo></mml:mrow></mml:mrow></mml:math> reconstruction observed by Raman spectroscopy. Physical Review B, 2007, 76, .	3.2	28
64	Confirmation of intrinsic electron gap states at nonpolar GaN(1-100) surfaces combining photoelectron and surface optical spectroscopy. Applied Physics Letters, 2014, 104, .	3.3	28
65	Growth mode of Bi and Sb layers on GaAs(110) and InP(110). Surface Science, 1991, 251-252, 621-627.	1.9	27
66	Effect of annealing on the band bending and the overlayer morphology at Sb/IIIâ€“V (110) interfaces. Applied Surface Science, 1992, 56-58, 169-177.	6.1	27
67	Vibrational modes of epitaxial monolayer adsorbates on semiconductor surfaces studied by Raman scattering. Journal of Electron Spectroscopy and Related Phenomena, 1993, 64-65, 85-94.	1.7	27
68	Analysis of semiconductor surface phonons by Raman spectroscopy. Applied Physics A: Materials Science and Processing, 1999, 69, 507-518.	2.3	27
69	Compositional dependence of Raman scattering and photoluminescence emission in CuxGaySe2 thin films. Journal of Applied Physics, 2003, 94, 4341-4347.	2.5	27
70	Molecule-solid interfaces studied with infrared ellipsometry: Ultrathin nitrobenzene films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1838.	1.6	26
71	Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682.	1.5	26
72	Surface phonons of the Si(111)-(<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 67 Td (xmlns:mml="http://www.w3.org/1998/Math/M reconstruction observed by Raman spectroscopy. Physical Review B, 2014, 89, .	3.2	26

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73	Study of clean and oxygen-covered Ag surfaces using optical reflectance anisotropy. Surface Science, 1997, 377-379, 388-392.	1.9	25
74	Atomic structure and composition of the P-rich InP(001) surfaces. Applied Surface Science, 2000, 166, 190-195.	6.1	25
75	Analysis of InAs(001) surfaces by reflectance anisotropy spectroscopy. Physical Review B, 2001, 64, .	3.2	25
76	Ordinary dielectric function of corundumlike <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î±</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> from 40ÂmeV to 20 eV. Physical Review Materials, 2018, 2, .	2.4	25
77	Microscopic structure of GaSb(001) c(2Ã—6) surfaces prepared by Sb decapping of MBE-grown samples. Physical Review B, 1997, 55, 15401-15404.	3.2	24
78	In situ surface passivation of IIIâ€“V semiconductors in MOVPE by amorphous As and P layers. Journal of Crystal Growth, 1997, 170, 230-236.	1.5	24
79	Optical properties of wurtziteAlxGa1â^'xN(x<0.1) parallel and perpendicular to thecaxis. Physical Review B, 2001, 64, .	3.2	24
80	Structure and interface composition of Co layers grown on As-rich GaAs(001) c(4Ã—4) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1591.	1.6	24
81	GaN and InN conduction-band states studied by ellipsometry. Physical Review B, 2008, 77, .	3.2	24
82	Surface structure of ordered InGaP(001): The(2Ã—4)reconstruction. Physical Review B, 2000, 62, 12601-12604.	3.2	23
83	Analysis of biosensors by chemically specific optical techniques. Chemiluminescence-imaging and infrared spectroscopic mapping ellipsometry. Analytical and Bioanalytical Chemistry, 2007, 387, 1823-1829.	3.7	23
84	Grand canonical Peierls transition in In/Si(111). Physical Review B, 2016, 93, .	3.2	23
85	Surface ordering on GaAs(100) by indium-termination. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1672.	1.6	22
86	Energy band structure and optical response function of icosahedral<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mtext>B</mml:mtext><mml:mrow><mml:mn>12</mml:mn></mml:mrow></mml:msu A spectroscopic ellipsometry and first-principles calculational study. Physical Review B, 2010, 81, .	3.2	22
87	Label-free biosensors based on in situ formed and functionalized microwires in microfluidic devices. Analyst, The, 2015, 140, 7896-7901.	3.5	22
88	The InP(110)/Sb interface: Ohmic behavior at large Sb coverages. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1044.	1.6	22
89	A reflectance anisotropy spectroscopy study of GaSb(100)c(2 Ã— 6) surfaces prepared by Sb decapping. Surface Science, 1996, 352-354, 771-775.	1.9	21
90	Angle Resolved Photoemission Spectroscopy of the InP(001) surface. Applied Surface Science, 2000, 166, 224-230.	6.1	21

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91	Growth phases and optical anisotropy of Co on preoxidized Cu(110). Physical Review B, 2001, 64, .	3.2	21
92	Optical resonances of indium islands on GaAs(001) observed by reflectance anisotropy spectroscopy. Physical Review B, 2003, 67, .	3.2	20
93	Ultrathin responsive polyelectrolyte brushes studied by infrared synchrotron mapping ellipsometry. Applied Physics Letters, 2008, 92, .	3.3	20
94	Optical properties of In₂O₃ from experiment and first-principles theory: influence of lattice screening. New Journal of Physics, 2018, 20, 053016.	2.9	20
95	Band structure and UV optical spectra of TGS crystals in the range of 4â€“10eV. Physica B: Condensed Matter, 2006, 373, 328-333.	2.7	19
96	An in situ XPS study of L-cysteine co-adsorbed with water on polycrystalline copper and gold. Applied Surface Science, 2018, 435, 870-879.	6.1	19
97	Optical properties of Sb-terminated GaAs and InP (110) surfaces. Physical Review B, 1995, 52, 12158-12167.	3.2	18
98	Influence of hydrogen adsorption on the optical properties of the GaAs(100)-c(4Ã—4) surface. Physical Review B, 1995, 51, 10923-10928.	3.2	18
99	Structure of InP (001) surfaces prepared by decapping and by ion bombardment and annealing. Physical Review B, 1997, 56, R1661-R1663.	3.2	18
100	Inâ€situ IR synchrotron mapping ellipsometry on stimuliâ€responsive PAAâ€bâ€PS/PEG mixed polymer brushes. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 197-199.	0.8	18
101	Negative spin-exchange splitting in the exciton fine structure of AlN. Applied Physics Letters, 2013, 102, .	3.3	18
102	Surface vibrational Raman modes of In:Si(111)(4Ã—1)and(8Ã—2)nanowires. Physical Review B, 2016, 94, .	3.2	18
103	A reflectance anisotropy spectroscopy study of molecular sulfur adsorption on the GaAs(100) surface. Journal of Applied Physics, 1995, 78, 1948-1952.	2.5	17
104	Optical anisotropies of InP(001) surfaces. Journal of Applied Physics, 1997, 81, 3611-3615.	2.5	17
105	Si(775)-Au atomic chains: Geometry, optical properties, and spin order. Physical Review Materials, 2017, 1, .	2.4	17
106	Optical Recognition of Atomic Steps on Surfaces. Physical Review Letters, 2003, 90, 177402.	7.8	16
107	Vibration eigenmodes of the Au- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mo>(</mml:mo><mml:mn>5</mml:mn><mml:mo>Ã—</mml:mo> /Si(111) surface studied by Raman spectroscopy and first-principles calculations. Physical Review B, 2016, 94, .	3.2	16
108	Gradient metal nanoislands as a unified surface enhanced Raman scattering and surface enhanced infrared absorption platform for analytics. Analyst, The, 2019, 144, 5271-5276.	3.5	16

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109	Hydrogen induced structure changes of GaAs(100) c(4 Ã— 4), (2 Ã— 4) and (4 Ã— 2) surfaces. Surface Science, 1996, 352-354, 66-70.	1.9	15
110	Reflectance Anisotropy Spectroscopy of Si(111)-(4 ï¿½ 1)-In. Physica Status Solidi A, 2001, 188, 1411-1416.	1.7	15
111	Atomic indium nanowires on Si(111): the (4 Ã— 1)â€“(8 Ã— 2) phase transition studied with reflectance anisotropy spectroscopy. Applied Surface Science, 2004, 234, 302-306.	6.1	15
112	A synchrotron-radiation-based variable angle ellipsometer for the visible to vacuum ultraviolet spectral range. Review of Scientific Instruments, 2014, 85, 055117.	1.3	15
113	A new concept of efficient therapeutic drug monitoring using the high-resolution continuum source absorption spectrometry and the surface enhanced Raman spectroscopy. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2018, 142, 91-96.	2.9	15
114	Vibration-Driven Self-Doping of Dangling-Bond Wires on Si(553)-Au Surfaces. Physical Review Letters, 2020, 124, 146802.	7.8	15
115	Optical characterization of surface electronic and vibrational properties of epitaxial antimony monolayers on IIIâ€“V (110) surfaces. Physica Status Solidi A, 1995, 152, 191-200.	1.7	14
116	VUV Ellipsometry on Beryllium Chalcogenides. Physica Status Solidi (B): Basic Research, 1999, 215, 15-20.	1.5	14
117	Surface vibrational modes of Sb-terminated (110) surfaces of III-V semiconductors investigated by Raman spectroscopy. Physical Review B, 2002, 66, .	3.2	14
118	Fourier Transform Infrared Synchrotron Ellipsometry for Studying the Anisotropy of Small Organic Samples. Applied Spectroscopy, 2003, 57, 1250-1253.	2.2	14
119	Surface phonons of Ge(001) and their correlation with the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>p</mml:mi></mml:math>(2<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 347 Td (xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>c</mml:mi>	3.2	14
120	Electronic and Optical Properties of Strontium Barium Niobate Single Crystals. Ferroelectrics, 2012, 426, 194-205.	0.6	14
121	Raman spectroscopy study of silicon nanoribbons on Ag(110). Applied Physics Letters, 2014, 104, 161612.	3.3	14
122	Spectrometer system using a modular echelle spectrograph and a laser-driven continuum source for simultaneous multi-element determination by graphite furnace absorption spectrometry. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2015, 107, 11-16.	2.9	14
123	Optical anisotropy of ordered Sb layers on III-V (110) surfaces. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 507-519.	0.6	13
124	First-principles study of InP and GaP(001) surfaces. Computational Materials Science, 2001, 22, 32-37.	3.0	13
125	Sb-induced(1Ã—1)reconstruction on Si(001). Physical Review B, 2003, 67, .	3.2	13
126	Oxidation- and organic-molecule-induced changes of the Si surface optical anisotropy:ab initiopredictions. Journal of Physics Condensed Matter, 2004, 16, S4323-S4334.	1.8	13

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127	Microfocus-infrared synchrotron ellipsometer for mapping of ultra thin films. Infrared Physics and Technology, 2006, 49, 74-77.	2.9	13
128	Metal-to-Insulator Transition in Au Chains on Si(111)-5Ã—2-Au by Band Filling: Infrared Plasmonic Signal and Ab Initio Band Structure Calculation. Journal of Physical Chemistry Letters, 2015, 6, 3615-3620.	4.6	13
129	Conductive single nanowires formed and analysed on microfluidic devices. Journal of Materials Chemistry C, 2016, 4, 9235-9244.	5.5	13
130	Electronic properties of Sb monolayers on IIIâ€“V(110) surfaces determined by resonance Raman scattering. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1481.	1.6	12
131	Hydrogen adsorption on the GaAs(001)-(2Ã—4) surface: A scanning-tunneling-microscopy study. Physical Review B, 1995, 52, 16337-16340.	3.2	12
132	Electric-field-induced Raman scattering in GaAs: Franz-Keldysh oscillations. Physical Review B, 1995, 51, 7353-7356.	3.2	12
133	InP(001) surface structure and interaction with atomic hydrogen. Applied Surface Science, 1998, 123-124, 228-232.	6.1	12
134	Ge/GaAs(001) interface formation investigated by reflectance anisotropy spectroscopy. Physical Review B, 1999, 59, 10657-10661.	3.2	12
135	Optical characterization of indium-terminated GaAs(001) surfaces. Physical Review B, 2000, 61, 1681-1684.	3.2	12
136	Preparation and structure of ultra-thin GaN (0001) layers on In0.11Ga0.89N-single quantum wells. Materials Science in Semiconductor Processing, 2016, 55, 7-11.	4.0	12
137	Controlling the Local Electronic Properties of Si(553)-Au through Hydrogen Doping. Physical Review Letters, 2018, 120, 166801.	7.8	12
138	Hydrogen interaction with Sb-terminated GaAs and InP (110) surfaces. Physical Review B, 1995, 52, 17379-17385.	3.2	11
139	Sb-mediated Ge growth on singular and vicinal Si(001) surfaces: A surface optical characterization study. Physical Review B, 2000, 62, 7378-7386.	3.2	11
140	Spectroscopic ellipsometry and reflectance anisotropy spectroscopy of biomolecular layers on silicon surfaces. Physica Status Solidi (B): Basic Research, 2005, 242, 2671-2680.	1.5	11
141	VUV-ellipsometry on GaN: Probing conduction band properties by core level excitations. Physica Status Solidi (B): Basic Research, 2005, 242, 2601-2609.	1.5	11
142	Metalâ€“insulator transition in Si(111)â€(4â€‰Ã—â€‰1)/(8â€‰Ã—â€‰2)â€studied by optical spectroscopy. Physica Status Solid (B): Basic Research, 2010, 247, 2033-2039.	1.5	11
143	Inversion of absorption anisotropy and bowing of crystal field splitting in wurtzite MgZnO. Applied Physics Letters, 2016, 108, .	3.3	11
144	Characterization of anisotropically shaped silver nanoparticle arrays via spectroscopic ellipsometry supported by numerical optical modeling. Applied Surface Science, 2017, 421, 460-464.	6.1	11

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